

74LVC3GU04

Triple inverter

Rev. 07 — 11 November 2009

Product data sheet

1. General description

The 74LVC3GU04 provides three inverters. Each inverter is a single stage with unbuffered output.

Inputs can be driven from either 3.3 V or 5 V devices. These features allow the use of these devices in a mixed 3.3 V and 5 V environment.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive at $V_{CC} = 3.0$ V
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Multiple package options
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C.

3. Ordering information

Table 1. Ordering information

Type number	Package				Version
	Temperature range	Name	Description		
74LVC3GU04DP	-40 °C to $+125$ °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm		SOT505-2
74LVC3GU04DC	-40 °C to $+125$ °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm		SOT765-1

Table 1. Ordering information ...continued

Type number	Package			
	Temperature range	Name	Description	Version
74LVC3GU04GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC3GU04GD	-40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
74LVC3GU04GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

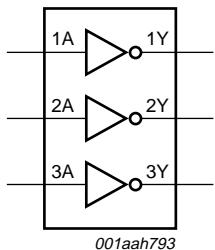
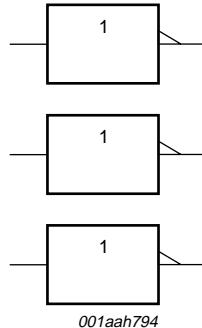
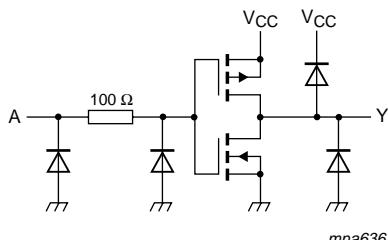
4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74LVC3GU04DP	VU04
74LVC3GU04DC	VU4
74LVC3GU04GT	VU4
74LVC3GU04GD	VU4
74LVC3GU04GM	VU4

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

**Fig 1.** Logic symbol**Fig 2.** IEC logic symbol**Fig 3.** Logic diagram (one gate)

6. Pinning information

6.1 Pinning

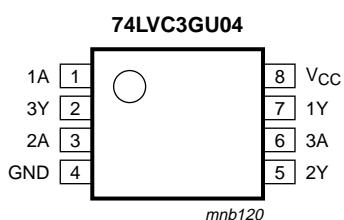


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

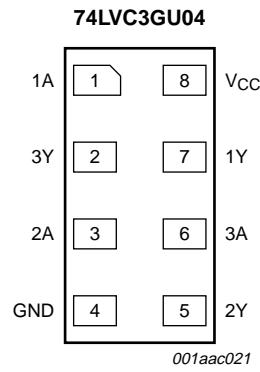


Fig 5. Pin configuration SOT833-1 (XSON8)

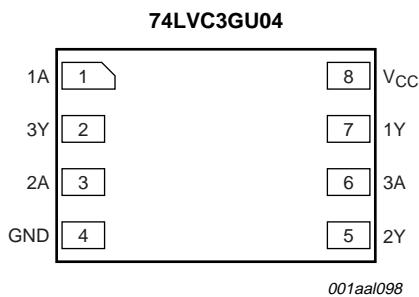


Fig 6. Pin configuration SOT996-2 (XSON8U)

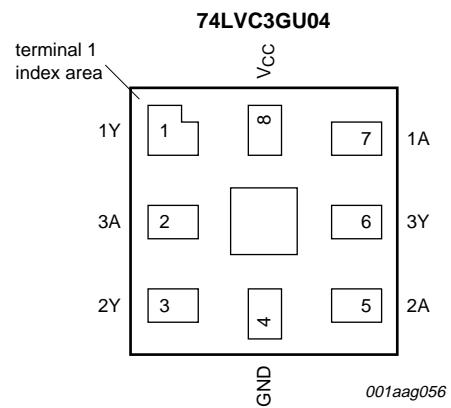


Fig 7. Pin configuration SOT902-1 (XQFN8U)

6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1 and SOT996-2	SOT902-1	
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output
V _{CC}	8	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input nA	Output nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
V _I	input voltage		^[1] -0.5	+6.5	V
V _O	output voltage	Active mode	^[1] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O > V _{CC} or V _O < 0 V	-	±50	mA
I _O	output current	V _O = 0 V to V _{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[2] -	250	mW
T _{stg}	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 packages: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
V _I	input voltage		0	5.5	V
V _O	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 2.7 V	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 5.5 V	0.75 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 5.5 V	-	-	0.25 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.3	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.8	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	µA
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	0.1	10	µA
C _I	input capacitance		-	5	-	pF
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 1.65 V to 5.5 V	0.8 × V _{CC}	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 5.5 V	-	-	0.2 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	0.95	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.7	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	1.9	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.0	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.4	-	-	V

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±20	µA
I _{CC}	supply current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	-	40	µA

[1] All typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V). For test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 8	[2]					
		V _{CC} = 1.65 V to 1.95 V	0.5	2.3	5.0	0.5	6.3	ns
		V _{CC} = 2.3 V to 2.7 V	0.3	1.8	4.0	0.3	4.0	ns
		V _{CC} = 2.7 V	0.3	2.6	4.5	0.3	5.6	ns
		V _{CC} = 3.0 V to 3.6 V	0.3	2.3	3.7	0.3	4.5	ns
		V _{CC} = 4.5 V to 5.5 V	0.3	1.7	3.0	0.3	3.8	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} ; V _{CC} = 3.3 V	[3]		7	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.[2] t_{pd} is the same as t_{PLH} and t_{PHL}.[3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).

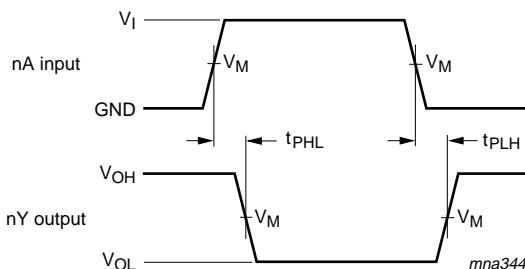
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$

f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



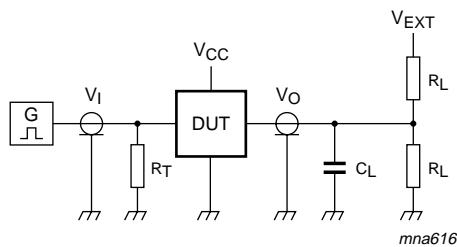
Measurement points are given in [Table 9](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 8. The input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 10](#).

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig 9. Load circuitry for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	$t_r = t_f$	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Additional characteristics

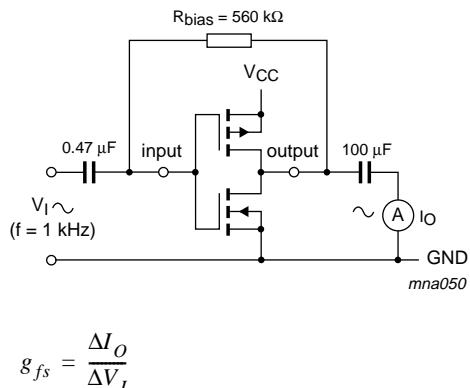


Fig 10. Test set-up for measuring forward transconductance

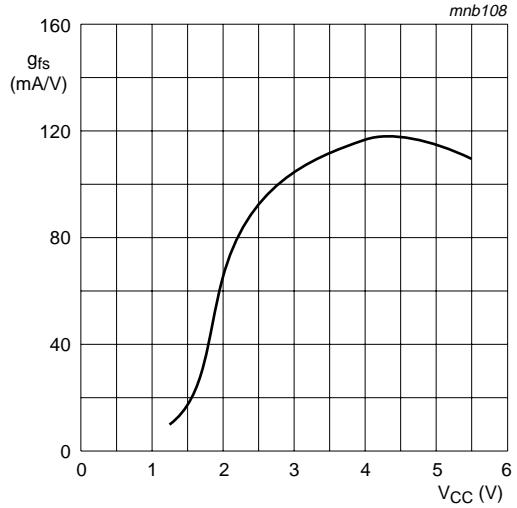
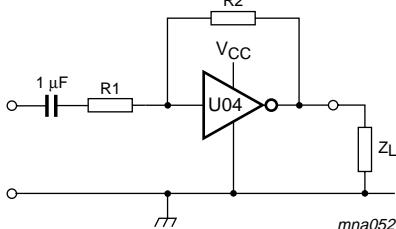


Fig 11. Typical forward transconductance as a function of supply voltage

14. Application information



$Z_L > 10 \text{ k}\Omega$

$R1 \geq 3 \text{ k}\Omega$

$R2 \leq 1 \text{ M}\Omega$

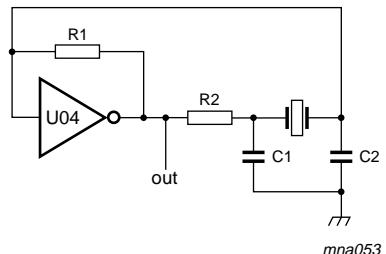
Open loop gain: $G_{ol} = 20$

$$\text{Voltage gain: } G_v = -\frac{G_{ol}}{1 + \frac{R1}{R2}(I + G_{ol})}$$

$V_{o(p-p)} = V_{CC} - 1.5 \text{ V}$ centered at $0.5 \times V_{CC}$

Unity gain bandwidth product is 5 MHz.

Fig 12. Linear amplifier application



$C1 = 47 \text{ pF}$

$C2 = 22 \text{ pF}$

$R1 = 1 \text{ M}\Omega$ to $10 \text{ M}\Omega$

$R2$ optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} ($I_{CC} = 2 \text{ mA}$ at $V_{CC} = 3.3 \text{ V}$ and $f = 10 \text{ MHz}$).

Fig 13. Crystal oscillator application

Remark: All values given are typical values unless otherwise specified.

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

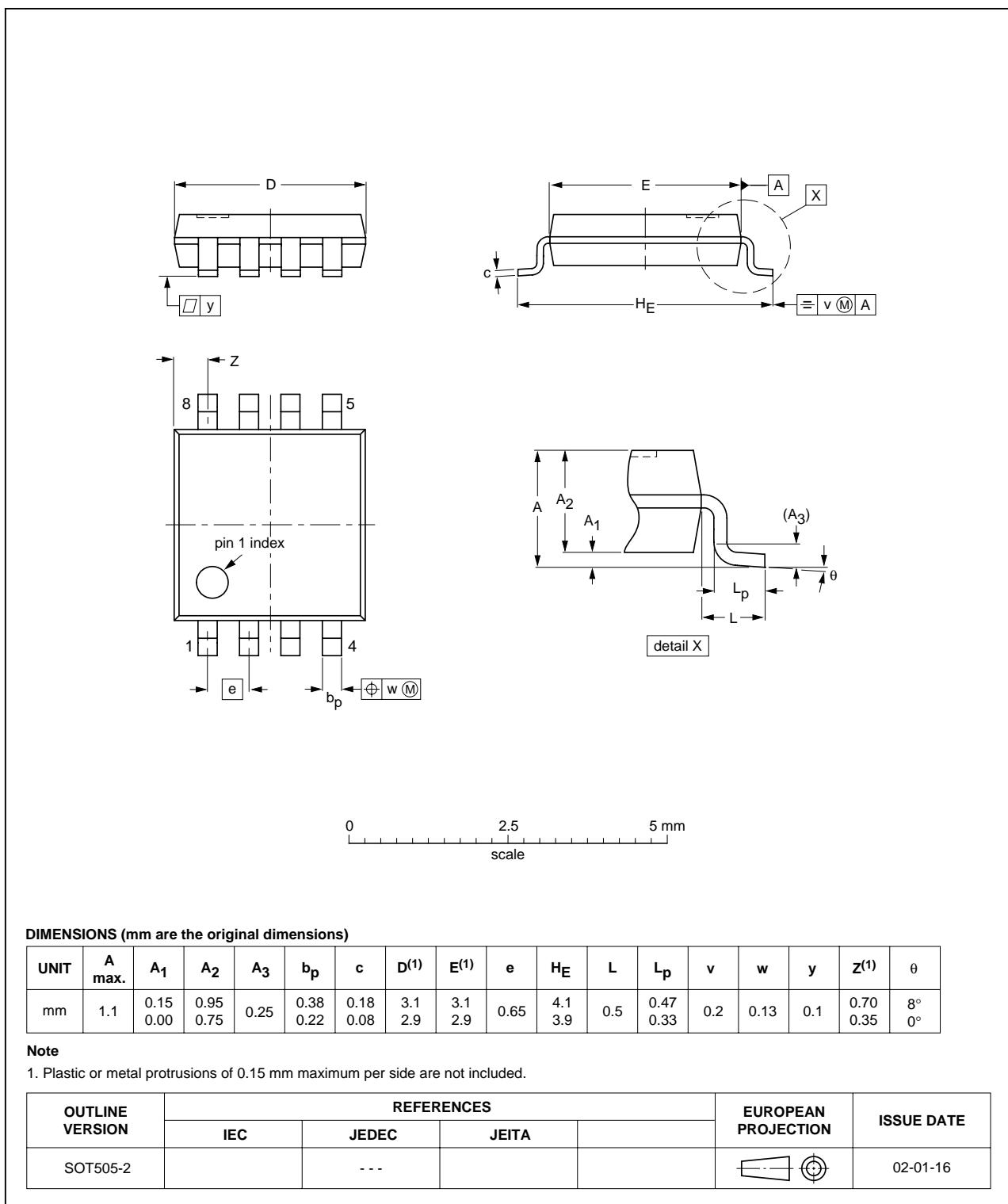


Fig 14. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

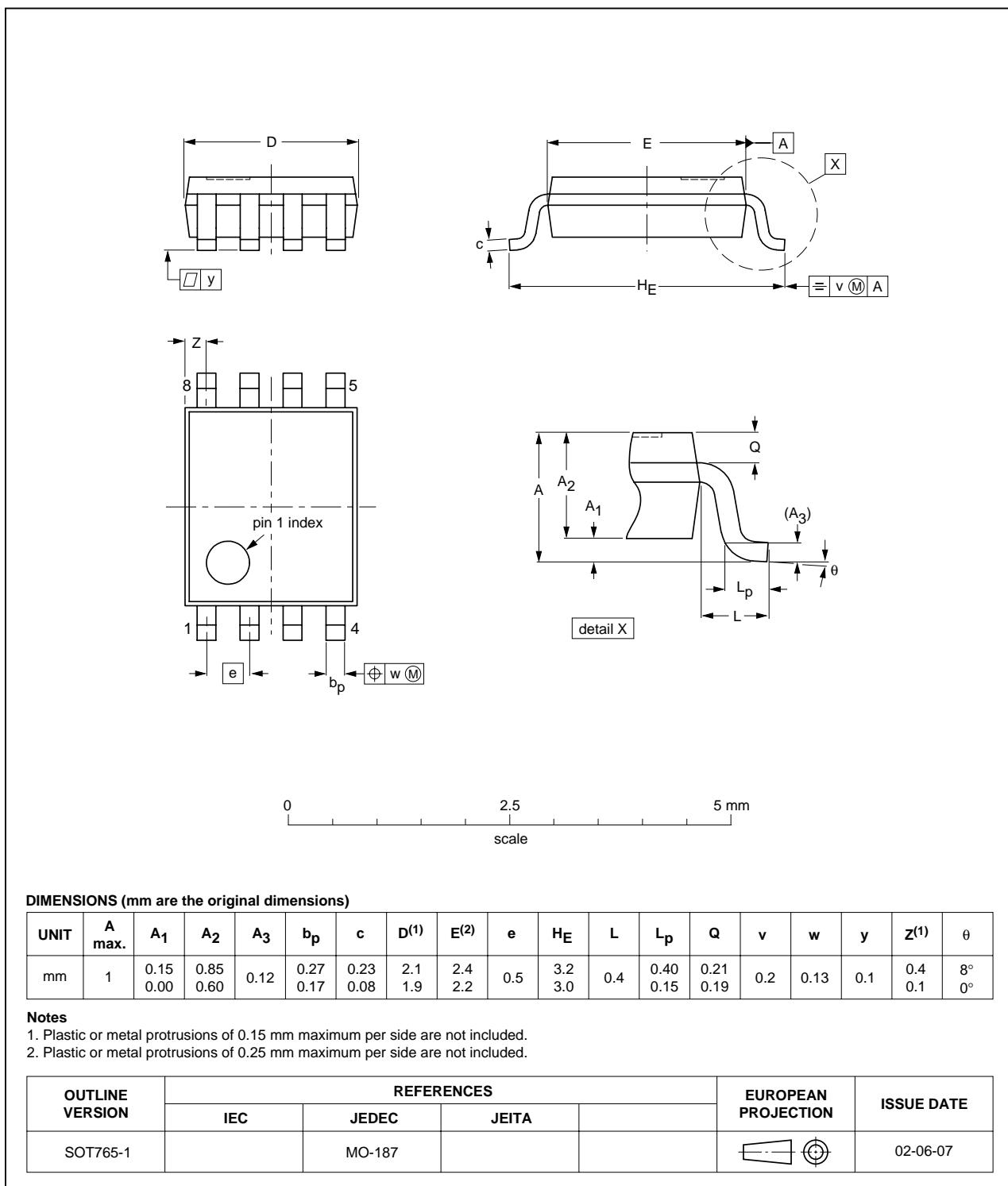


Fig 15. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body $1 \times 1.95 \times 0.5$ mm

SOT833-1

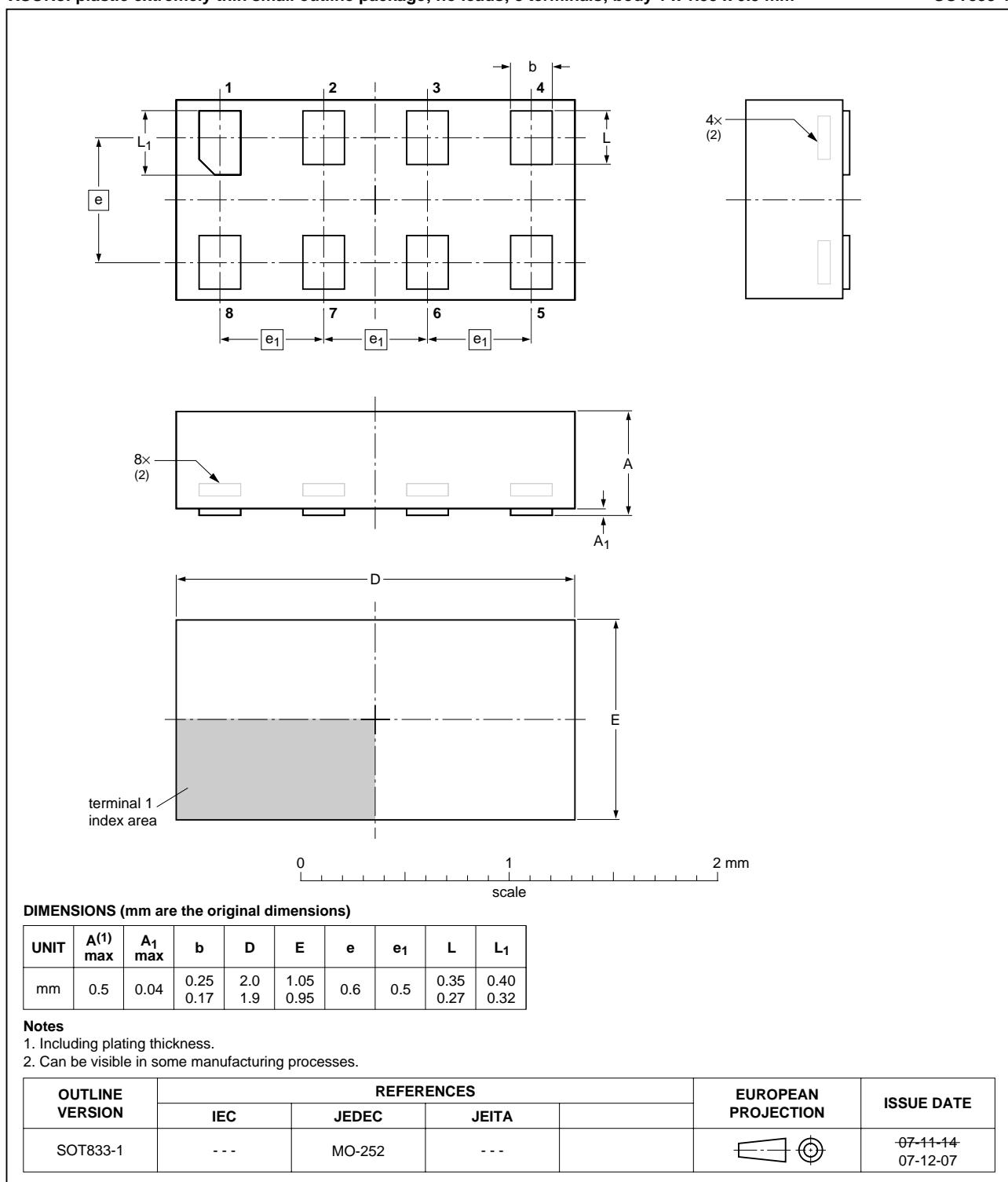


Fig 16. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

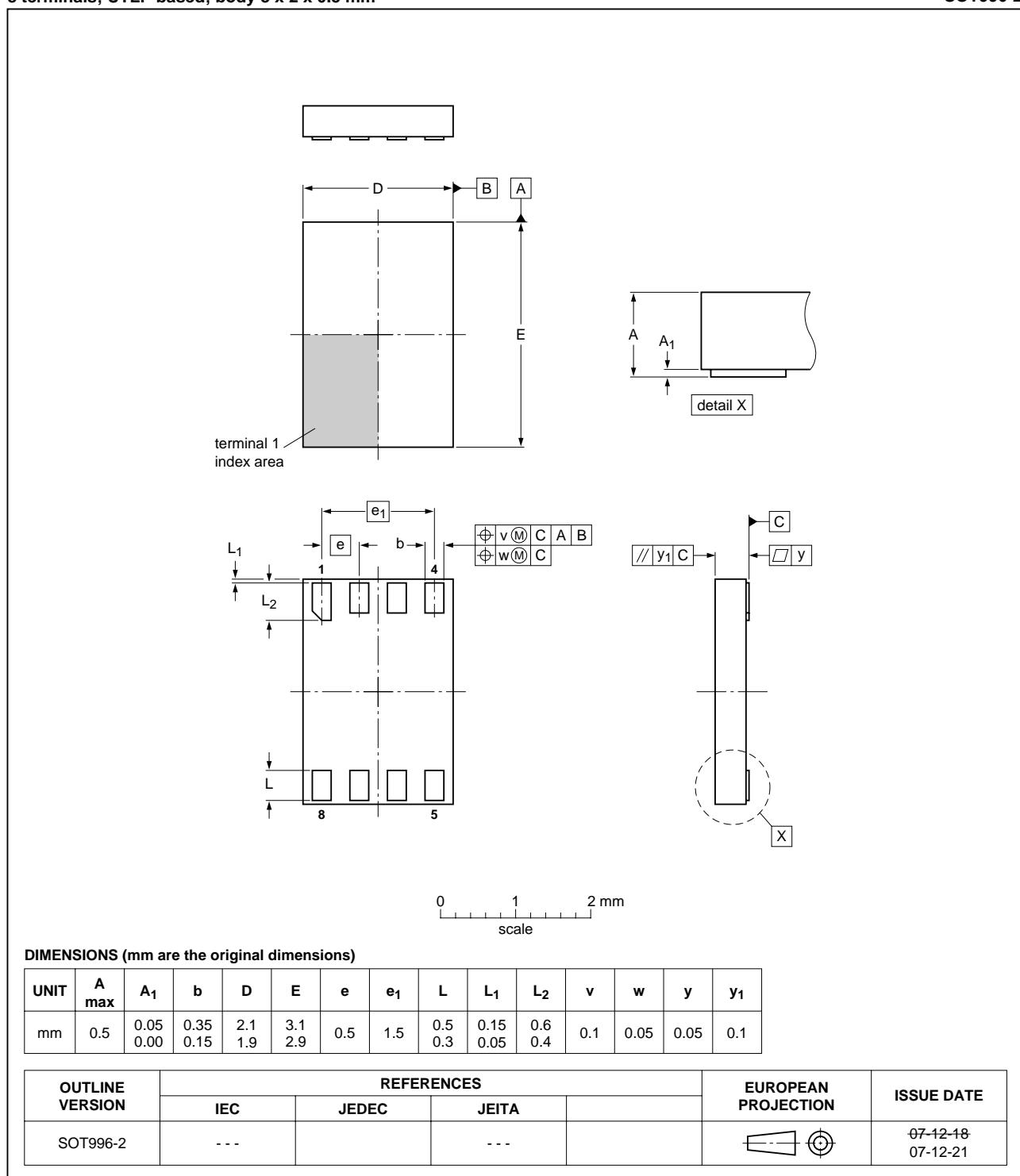


Fig 17. Package outline SOT996-2 (XSON8U)

XQFN8U: plastic extremely thin quad flat package; no leads;
8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

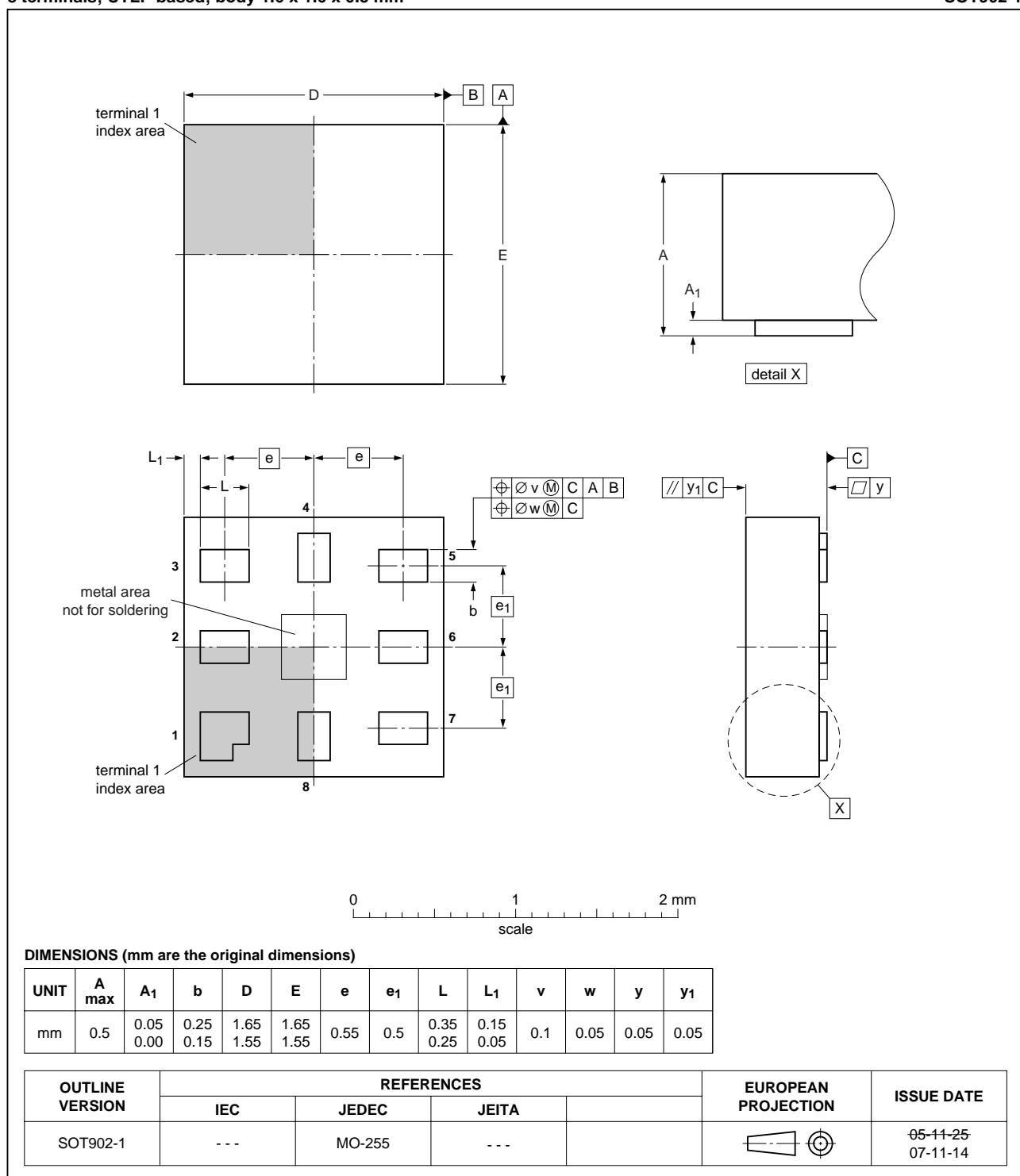


Fig 18. Package outline SOT902-1 (XQFN8U)

16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

17. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC3GU04_7	20091111	Product data sheet	-	74LVC3GU04_6
Modifications:	<ul style="list-style-type: none"> • Added type number 74LVC3GU04GD (XSON8U package) 			
74LVC3GU04_6	20080304	Product data sheet	-	74LVC3GU04_5
74LVC3GU04_5	20071005	Product data sheet	-	74LVC3GU04_4
74LVC3GU04_4	20070315	Product data sheet	-	74LVC3GU04_3
74LVC3GU04_3	20050201	Product data sheet	-	74LVC3GU04_2
74LVC3GU04_2	20041027	Product data sheet	-	74LVC3GU04_1
74LVC3GU04_1	20040512	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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